AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method of making a semiconductor structure, comprising:

~~determining~~ calculating a first polish time, sufficient to planarize a layer on a semiconductor substrate;

polishing the layer for said first polish time, to planarize the layer; and

polishing the layer to a predetermined thickness.

2. (Currently Amended) The method of claim 1, further comprising, prior to the calculating ~~determining~~ of said first polish time, measuring the thickness of the layer.

3. (Currently Amended) The method of claim 1, further comprising, prior to the calculating ~~determining~~ of said first polish time, measuring ~~the~~ a pattern density of the layer.

4. (Currently Amended) The method of claim 1, further comprising, prior to the calculating ~~determining~~ of said first polish time, identifying ~~the~~ a composition of the layer.

5. (Original) The method of claim 1, further comprising determining a second polish time sufficient to reduce the thickness of the layer after planarization to the predetermined thickness;

wherein the polishing of the layer to the predetermined thickness comprises polishing the layer for said second polish time.

6. (Currently Amended) A process for making a plurality of semiconductor structures, comprising

making each semiconductor structure by the method of claim 1;

wherein ~~the~~ a Cpk of the process is at least 1.

7. (Currently Amended) A process for making a plurality of semiconductor structures, comprising:

making each semiconductor structure by the method of claim 5;

wherein ~~the~~ a Cpk of the process is at least 1.

8. (Currently Amended) The process of claim 7, wher in the making of each semiconductor structure comprises, prior to the calculating ~~determining~~ of said first polish time, measuring the thickness of the layer, ~~the~~ a pattern density of the layer, and identifying ~~the~~ a composition of the layer.

9-11. (Cancelled)

12. (Currently Amended) In a method of making a semiconductor structure, including polishing a layer by chemical mechanical polishing, the improvement comprising ~~determining~~ calculating a first polish time sufficient to make the layer planar; determining a second polish time to reduce the thickness of the planar layer; and polishing for a third polish time equal to the sum of the first and second polish times.

13. (Original) A method of making a semiconductor device, comprising:
making a semiconductor structure by the method of claim 1; and
forming a semiconductor device from said structure.

14. (Original) A method of making an electronic device, comprising:
making a semiconductor device by the method of claim 13; and
forming an electronic device, comprising said semiconductor device.

15. (Original) A method of making a semiconductor device, comprising:
making a semiconductor structure by the method of claim 5; and
forming a semiconductor device from said structure.

16. (Original) A method of making an electronic device, comprising:
making a semiconductor device by the method of claim 15; and
forming an electronic device, comprising said semiconductor device.

17-23. (Cancelled)

24. (Currently Amended) A method of making a semiconductor structure, comprising:

polishing a layer on a semiconductor substrat with ~~the~~ a system, comprising:

a chemical mechanical polishing apparatus; and

machine readable medium, comprising code, imbedded in the machine readable medium, for calculating a first polish time, sufficient to planarize a layer on a semiconductor substrate. ~~of claim 23.~~

25. (Original) A method of making a semiconductor device, comprising: making a semiconductor structure by the method of claim 24; and forming a semiconductor device from said structure.

26. (Original) A method of making an electronic device, comprising: making a semiconductor device by the method of claim 25; and forming an electronic device, comprising said semiconductor device.